

# **PSMN8R5-100ES**

N-channel 100 V 8.5 mΩ standard level MOSFET in I2PAK
11 October 2012 Product data sheet

### 1. Product profile

#### 1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- · Synchronous rectification

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>j</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static charac	cteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12		-	6.4	8.5	mΩ
Dynamic cha	aracteristics						
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V;		-	33	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	111	-	nC
Avalanche R	uggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 100 V; $R_{GS}$ = 50 Ω; unclamped; Fig. 3		-	-	219	mJ

[1] Continious current limited by package.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G—U: 4
mb	D	mounting base; connected to drain		mbb076 S
			I2PAK (SOT226)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN8R5-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226		

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN8R5-100ES	PSMN8R5-100ES

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>		-	75	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; Fig. 4		-	429	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	263	W
T <sub>stg</sub>	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode					,
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	429	Α
Avalanche	Ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup} \le$ 100 V; $R_{GS}$ = 50 Ω; unclamped; Fig. 3		-	219	mJ

#### [1] Continious current limited by package.

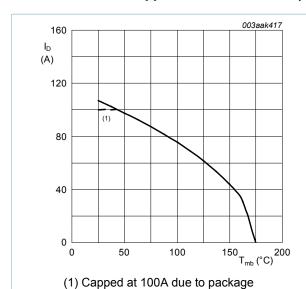


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 V$ 

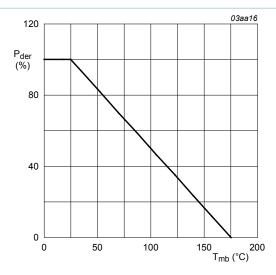


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

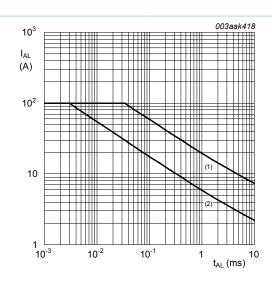


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) 
$$T_{j (init)} = 25$$
°C; (2)  $T_{j (init)} = 130$ °C

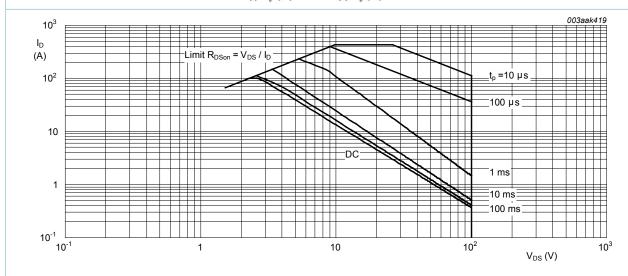


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

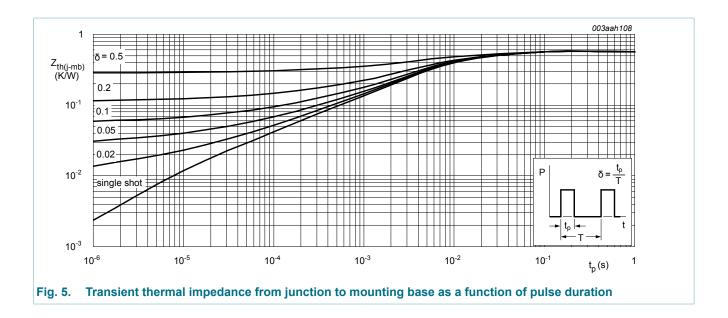
#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W	

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#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub> drain-source		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I <sub>DSS</sub> drain	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.02	1	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 100 °C	-	-	20	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	-	-	22.6	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; Fig. 12	-	-	14.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12	-	6.4	8.5	mΩ
$R_G$	gate resistance	f = 1 MHz	-	0.71	-	Ω

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;	-	111	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 14; Fig. 15	-	24	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	16	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	8	-	nC
$Q_{GD}$	gate-drain charge		-	33	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 50 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	4.4	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16; Fig. 17$	-	5512	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; Fig. 16	-	380	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u> ; <u>Fig. 17</u>	-	256	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V;	-	20	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	35	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	87	-	ns
t <sub>f</sub>	fall time		-	43	-	ns
Source-drai	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 18$	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	53	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V	-	124	-	nC

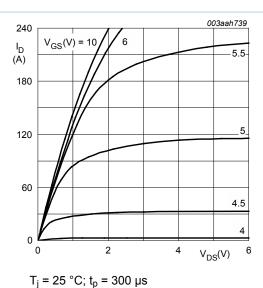


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

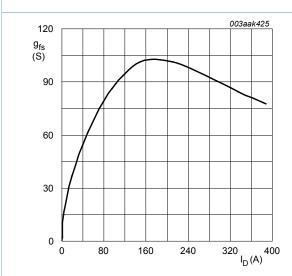


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; \ V_{DS} = 10V$$

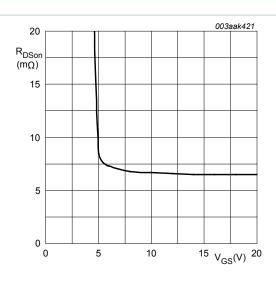


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 25$ A

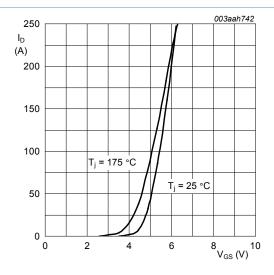


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

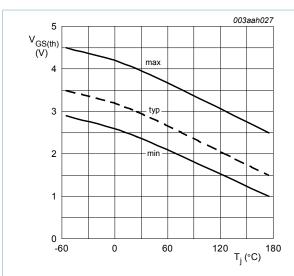


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

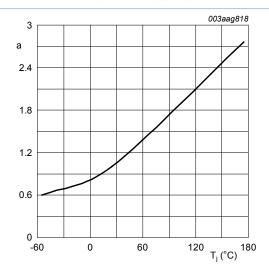


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25 \, \text{C})}}$$

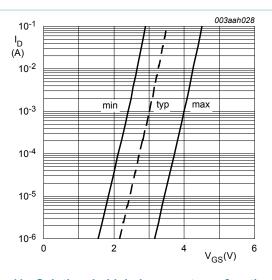


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

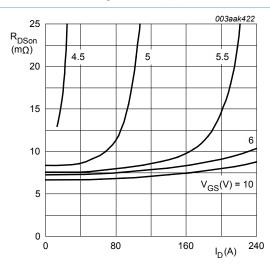


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

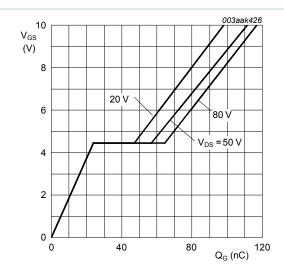
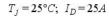


Fig. 14. Gate-source voltage as a function of gate charge; typical values



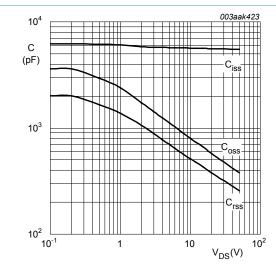


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Input and reverse transfer capacitances as a as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

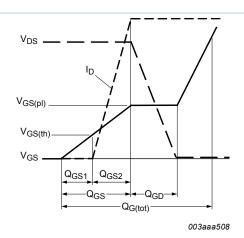
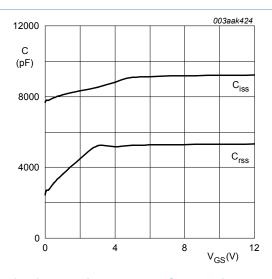


Fig. 15. Gate charge waveform definitions



function of gate-source voltage, typical values

$$\mathbf{f} = \mathbf{1}$$
 MHz;  $V_{DS} = \mathbf{0}$  V

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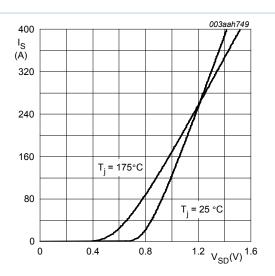


Fig. 18. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

### 8. Package outline

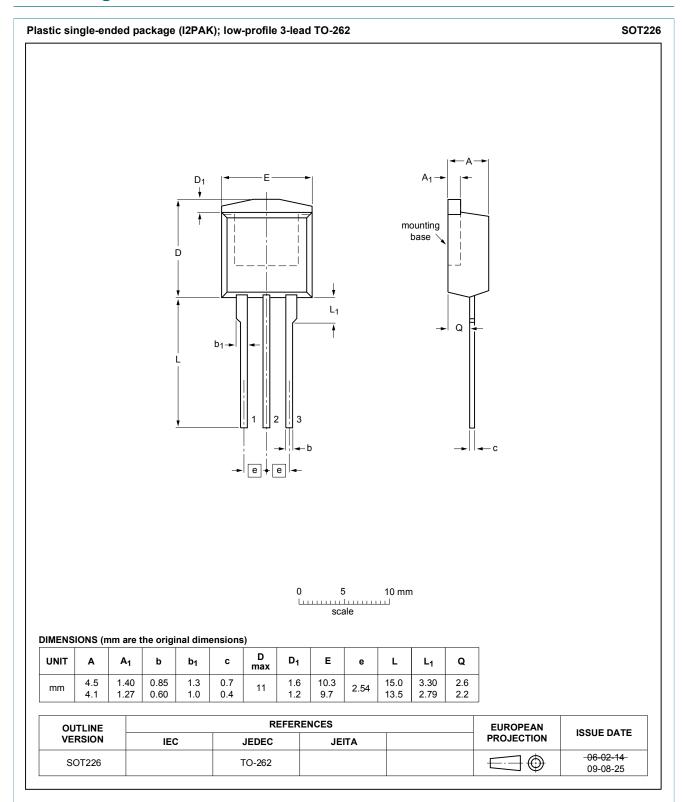


Fig. 19. Package outline I2PAK (SOT226)

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#### 9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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